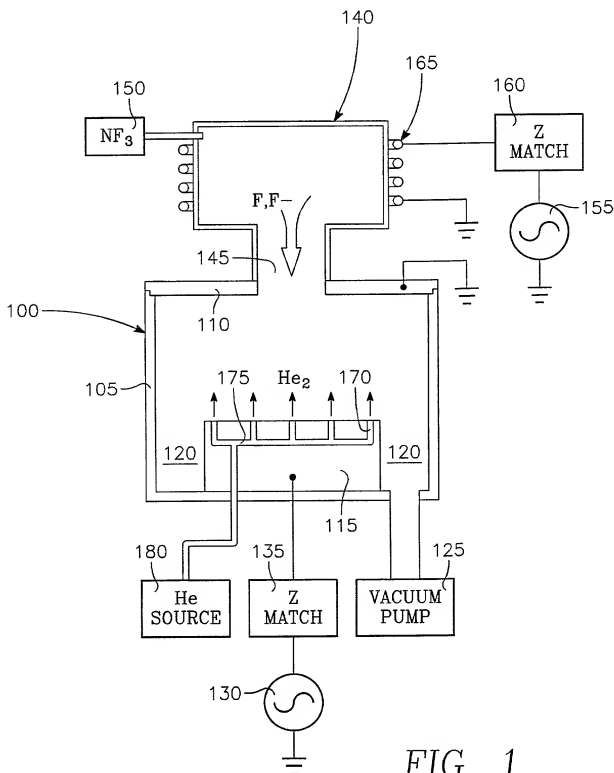


EFFICIENT CLEANING BY SECONDARY IN-SITU ACTIVATION  
OF ETCH PRECURSOR FROM REMOTE PLASME SOURCE  
DOCKET: 6408

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EFFICIENT CLEANING BY SECONDARY IN-SITU ACTIVATION  
OF ETCH PRECURSOR FROM REMOTE PLASME SOURCE  
DOCKET: 6408

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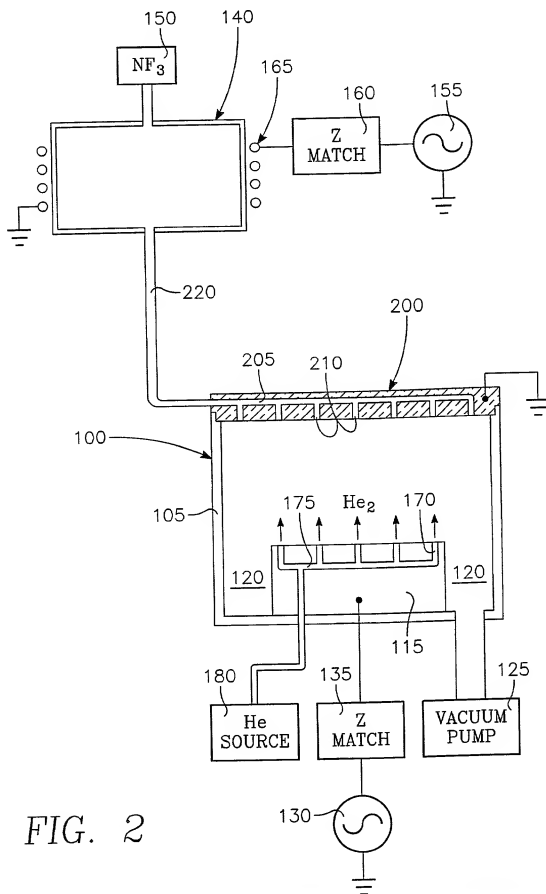


FIG. 2

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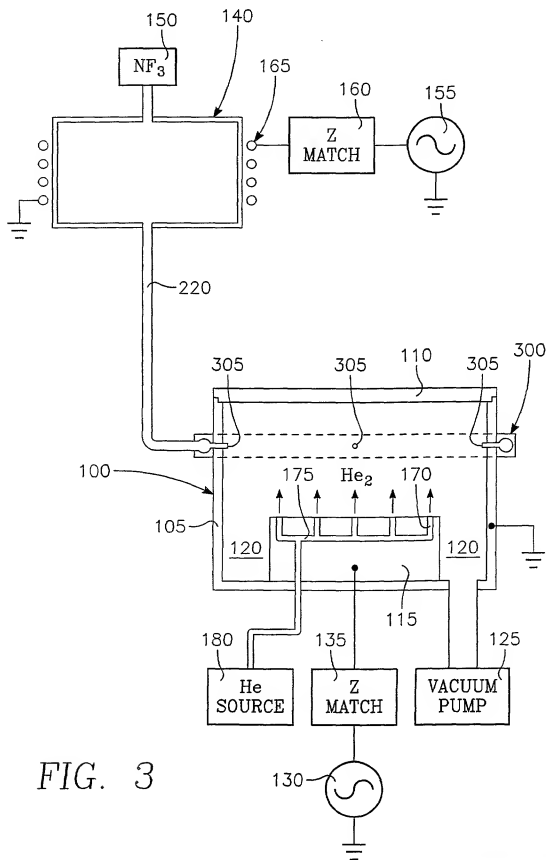


FIG. 3

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EFFICIENT CLEANING BY SECONDARY IN-SITU ACTIVATION  
OF ETCH PRECURSOR FROM REMOTE PLASMA SOURCE  
DOCKET: 6408

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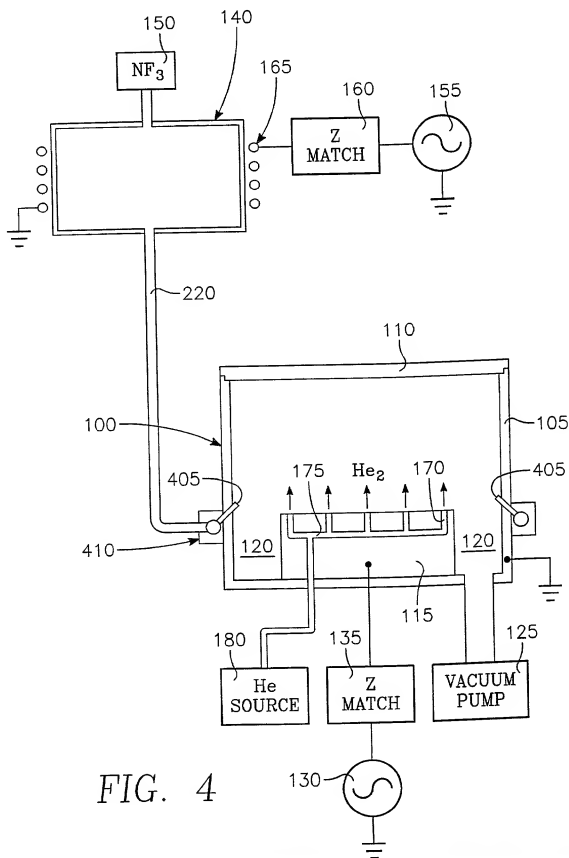


FIG. 4

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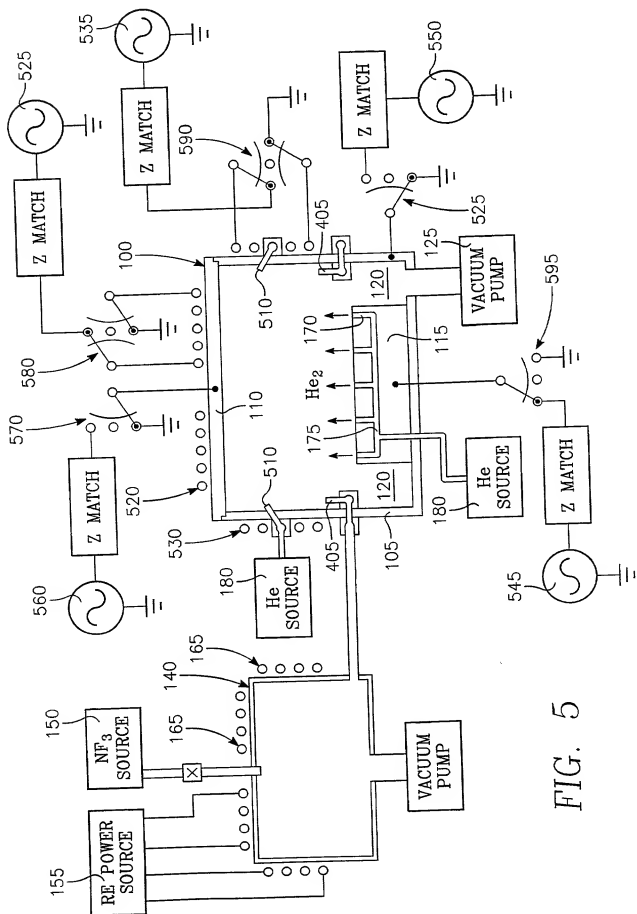


FIG. 5

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